

Abstract Submitted
for the MAR14 Meeting of
The American Physical Society

Observation of microwave-induced resistance oscillations in high-mobility 2D hole gas in sGe/SiGe quantum wells Q.A. EBNER, P.D. MARTIN, Q. SHI, M.A. ZUDOV, School of Physics and Astronomy, University of Minnesota, Minneapolis, Minnesota 55455, USA, O.A. MIRONOV, R.J.H. MORRIS, D.R. LEADLEY, University of Warwick, Coventry, CV4 7AL, UK — Microwave-induced resistance oscillations (MIRO) have been extensively studied for more than a decade but, until now, have remained unique to GaAs/AlGaAs-based 2D electron systems. In this talk we report on the observation of MIRO in a very different setting, a 2D hole gas hosted in strained Ge/SiGe quantum wells. These findings demonstrate that MIRO is a universal phenomenon and that microwave photoresistance can be utilized to probe the energy spectrum and the correlation effects of 2D holes in Ge/SiGe quantum wells.

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Date submitted: 15 Nov 2013

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